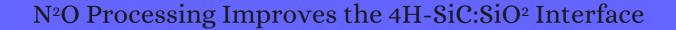
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#	Paper	IF	Citations
158	Nitrogen passivation of deposited oxides on n 4HBiC. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 4266-4268	3.4	20
157	Development of high-current 4H-SiC ACCUFET. <i>IEEE Transactions on Electron Devices</i> , <b>2003</b> , 50, 471-478	2.9	14
156	Effects of Nitrogen Radical Irradiation on Performance of SiC MOSFETs. <i>Materials Science Forum</i> , <b>2003</b> , 433-436, 945-948	0.4	
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131 130 129 128	High Temperature Rapid Thermal Oxidation and Nitridation of 4H-SiC in Diluted N2O and NO Ambient. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 669-672  Effects of N2O Anneal on Channel Mobility of 4H-SiC MOSFET and Gate Oxide Reliability. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 697-700  Characteristics of Post-Nitridation Rapid-Thermal Annealed Gate Oxide Grown on 4H-SiC. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 689-692  Low On-Resistance in Normally-Off 4H-SiC Accumulation MOSFET. <i>Materials Science Forum</i> , <b>2005</b> , 483-485, 817-820	0.4	15 4 4
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20	Reduction of interface state density in SiC (0001) MOS structures by low-oxygen-partial-pressure annealing. <i>Applied Physics Express</i> , <b>2019</b> , 12, 031001	2.4	12
19	Effect of quantum confinement on the defect-induced localized levels in 4H-SiC(0001)/SiO2 systems. <i>Journal of Applied Physics</i> , <b>2020</b> , 128, 095702	2.5	5
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17	. IEEE Transactions on Electron Devices, <b>2021</b> , 68, 288-293	2.9	3
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14	Properties of Nitrided Oxides on SiC. Advanced Texts in Physics, 2004, 373-386		8	
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11	Design and formation of SiC (0001)/SiO2 interfaces via Si deposition followed by low-temperature oxidation and high-temperature nitridation. <i>Applied Physics Express</i> , <b>2020</b> , 13, 091003	2.4	17	
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8	Development of SiC Diodes, Power MOSFETs and Intelligent Power Modules. 291-319			
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